

2SK2796(L), 2SK2796(S)

Silicon N Channel MOS FET
High Speed Power Switching

REJ03G1034-0500
(Previous: ADE-208-534C)
Rev.5.00
Sep 07, 2005

Features

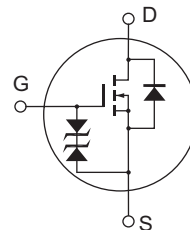
- Low on-resistance
 $R_{DS(on)} = 0.12 \Omega$ typ.
- 4 V gate drive devices.
- High speed switching

Outline

RENESAS Package code: PRSS0004ZD-A
(Package name: DPAK(L)-(1))



RENESAS Package code: PRSS0004ZD-C
(Package name: DPAK(S))



1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	60	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	5	A
Drain peak current	$I_{D(pulse)}$ ^{Note1}	20	A
Body-drain diode reverse drain current	I_{DR}	5	A
Avalanche current	I_{AP} ^{Note3}	5	A
Avalanche energy	E_{AR} ^{Note3}	2.14	mJ
Channel dissipation	P_{ch} ^{Note2}	20	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

Notes: 1. $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$
 2. Value at $T_c = 25^\circ C$
 3. Value at $T_{ch} = 25^\circ C$, $R_g \geq 50 \Omega$

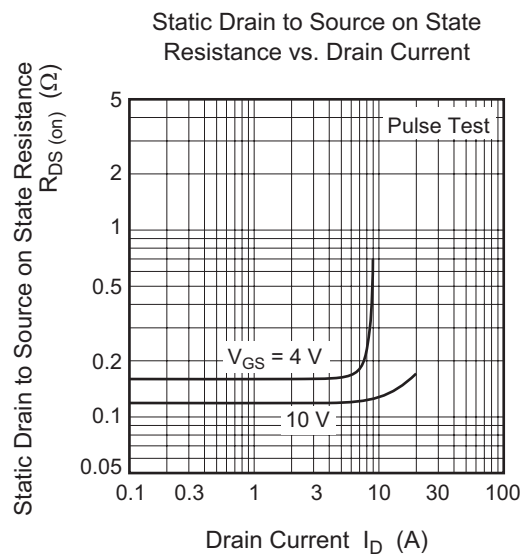
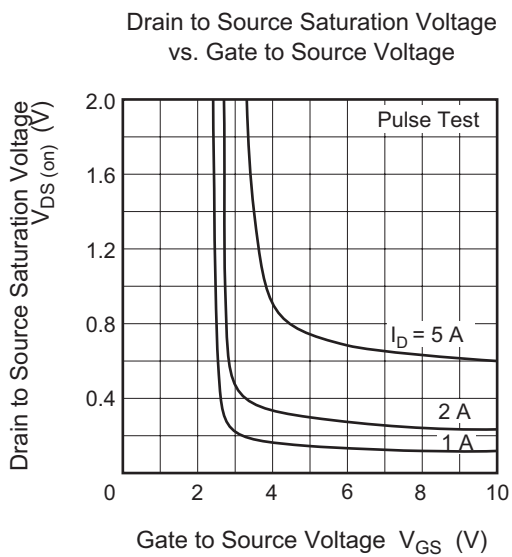
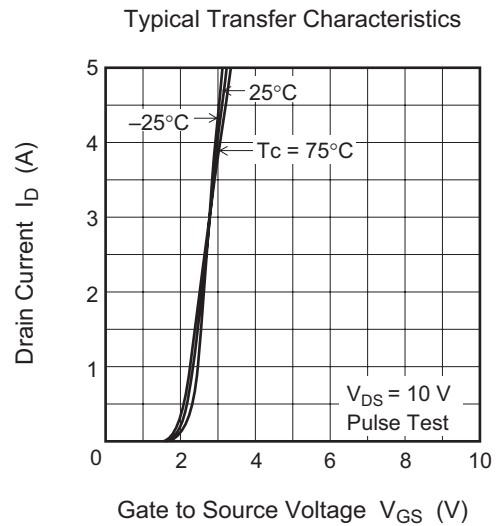
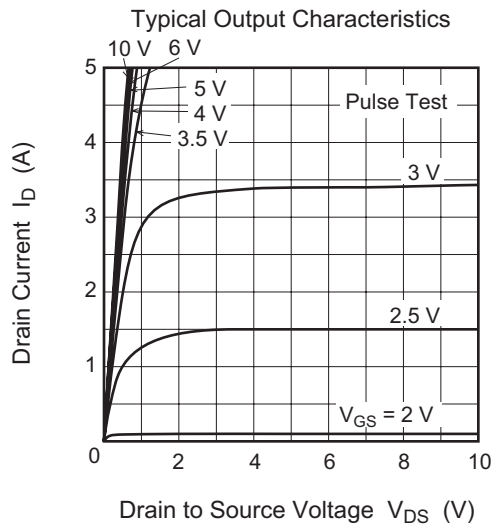
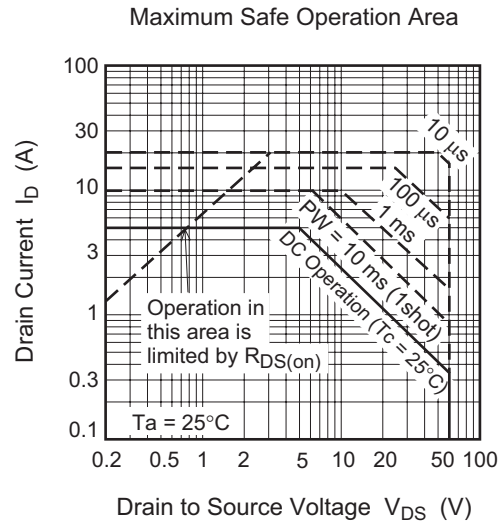
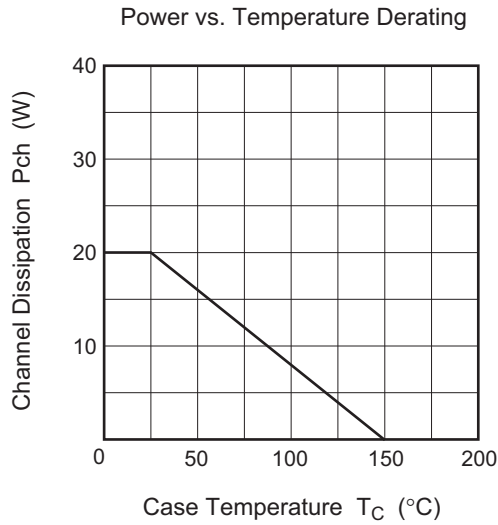
Electrical Characteristics

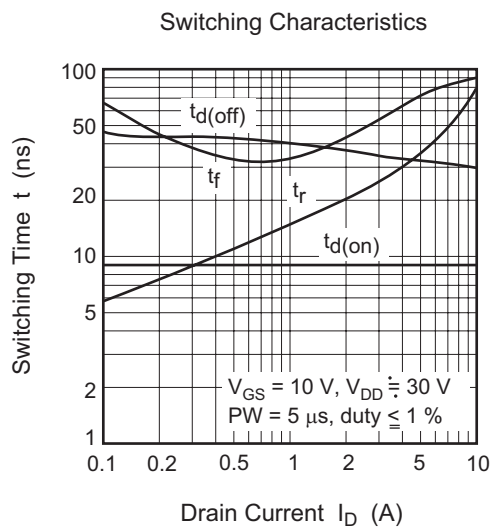
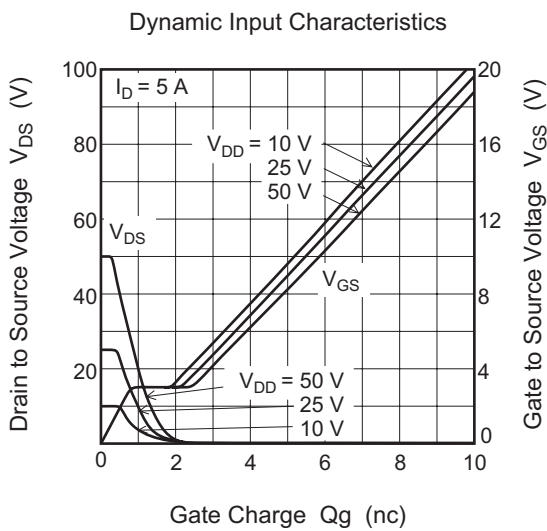
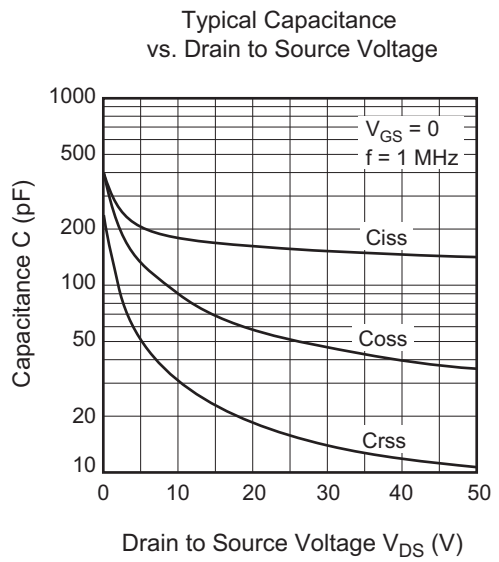
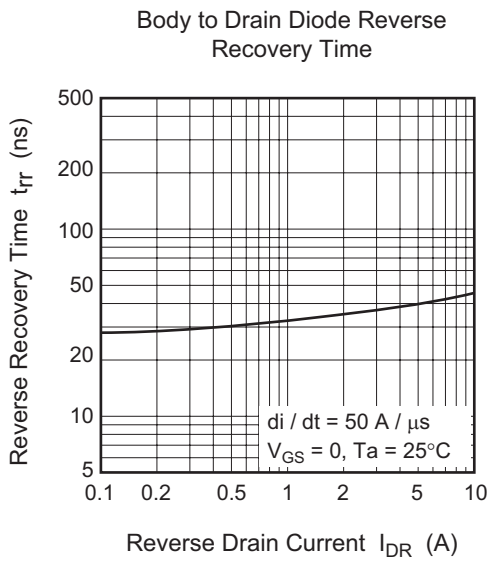
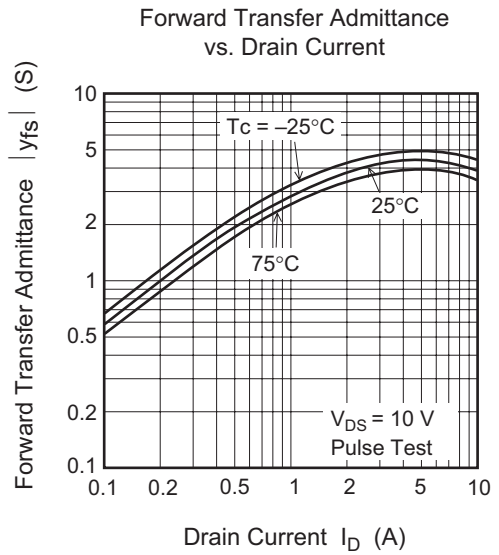
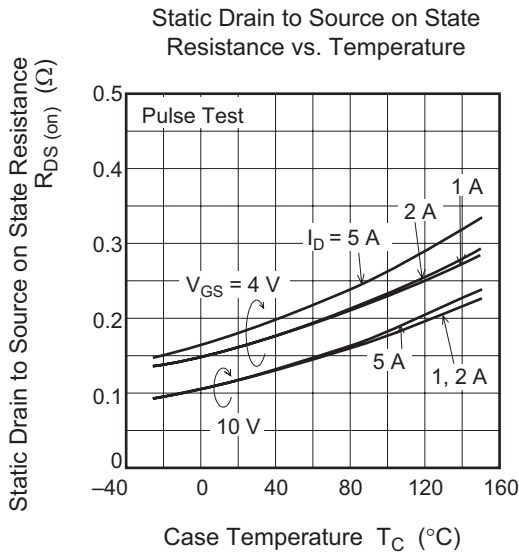
(Ta = 25°C)

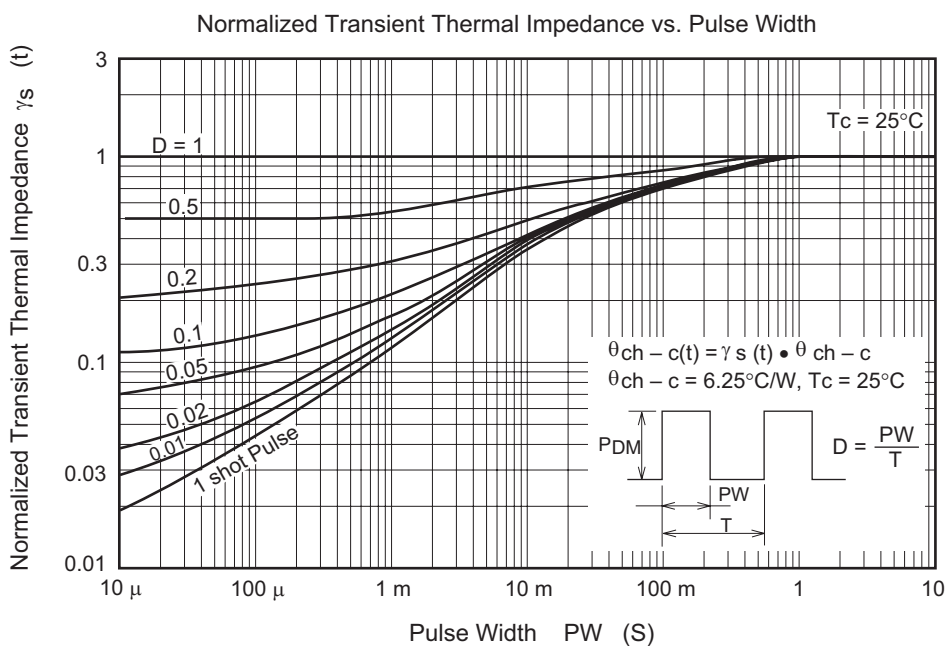
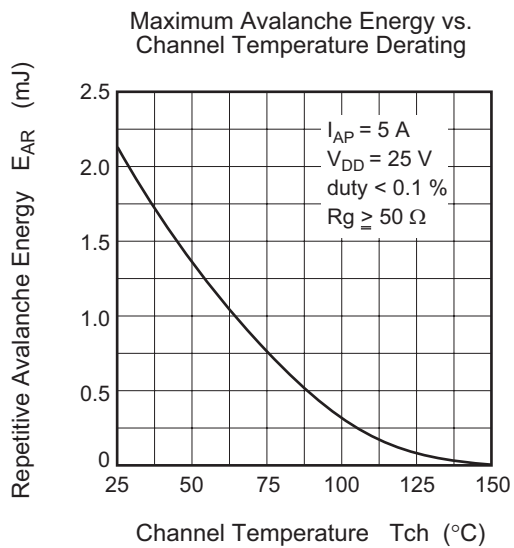
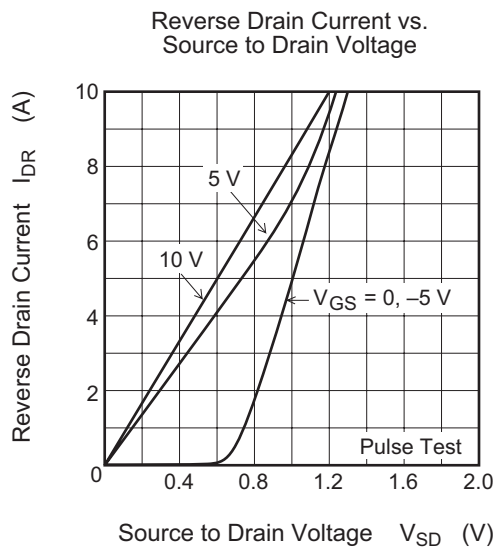
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	60	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	10	μA	$V_{DS} = 60 \text{ V}$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±10	μA	$V_{GS} = \pm 16 \text{ V}$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	1.0	—	2.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	0.12	0.16	Ω	$I_D = 3 \text{ A}$, $V_{GS} = 10 \text{ V}$ ^{Note4}
	$R_{DS(on)}$	—	0.16	0.25	Ω	$I_D = 3 \text{ A}$, $V_{GS} = 4 \text{ V}$ ^{Note4}
Forward transfer admittance	$ y_{fs} $	2.5	4.0	—	S	$I_D = 3 \text{ A}$, $V_{DS} = 10 \text{ V}$ ^{Note4}
Input capacitance	C_{iss}	—	180	—	pF	$V_{DS} = 10 \text{ V}$, $V_{GS} = 0$, $f = 1 \text{ MHz}$
Output capacitance	C_{oss}	—	90	—	pF	
Reverse transfer capacitance	C_{rss}	—	30	—	pF	
Turn-on delay time	$t_{d(on)}$	—	9	—	ns	$V_{GS} = 10 \text{ V}$, $I_D = 3 \text{ A}$, $R_L = 10 \Omega$
Rise time	t_r	—	25	—	ns	
Turn-off delay time	$t_{d(off)}$	—	35	—	ns	
Fall time	t_f	—	55	—	ns	
Body-drain diode forward voltage	V_{DF}	—	1.0	—	V	$I_F = 5 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	40	—	ns	$I_F = 5 \text{ A}$, $V_{GS} = 0$ $di_F/dt = 50 \text{ A}/\mu s$

Note: 4. Pulse test

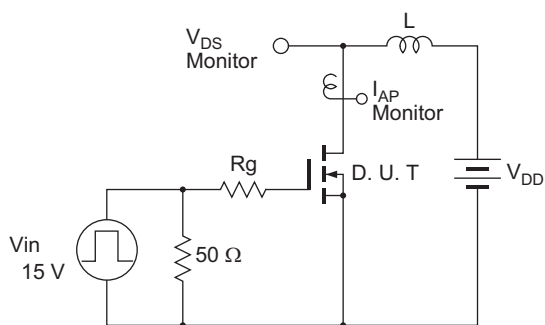
Main Characteristics



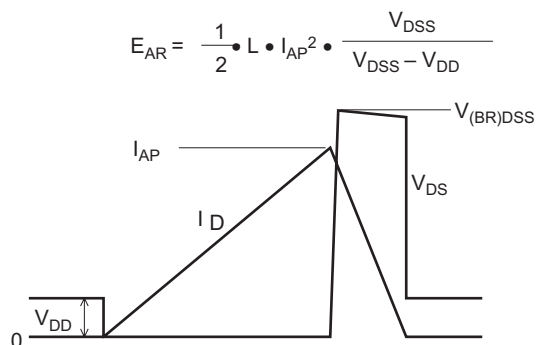


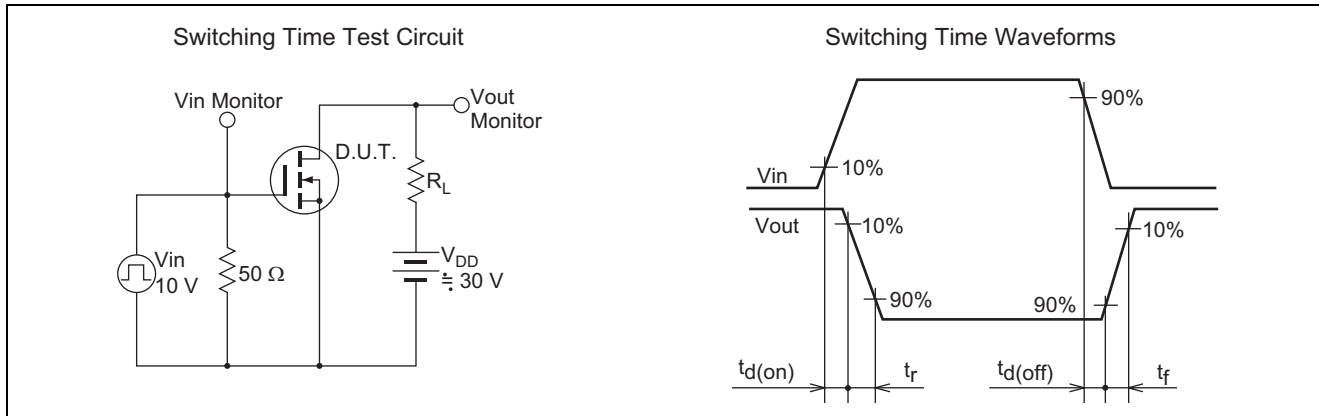


Avalanche Test Circuit

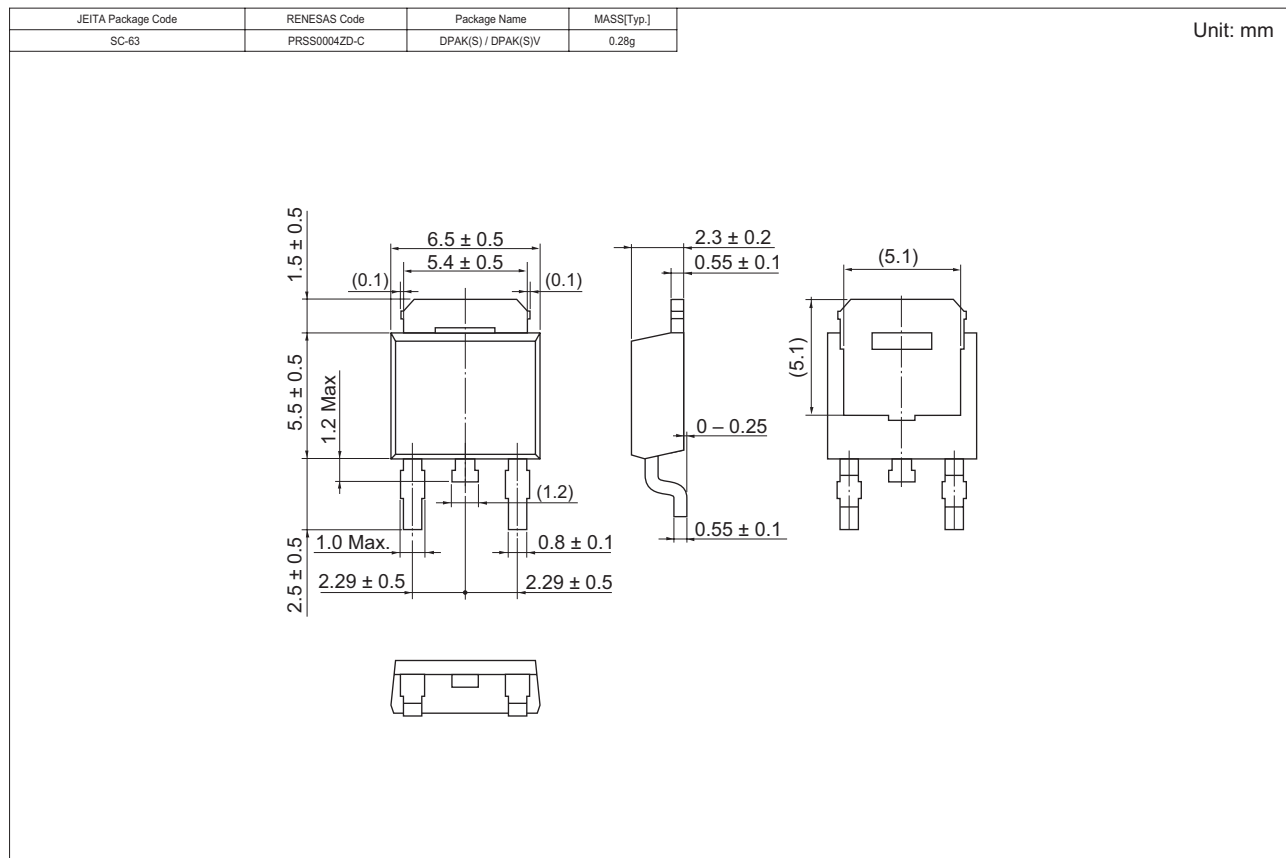
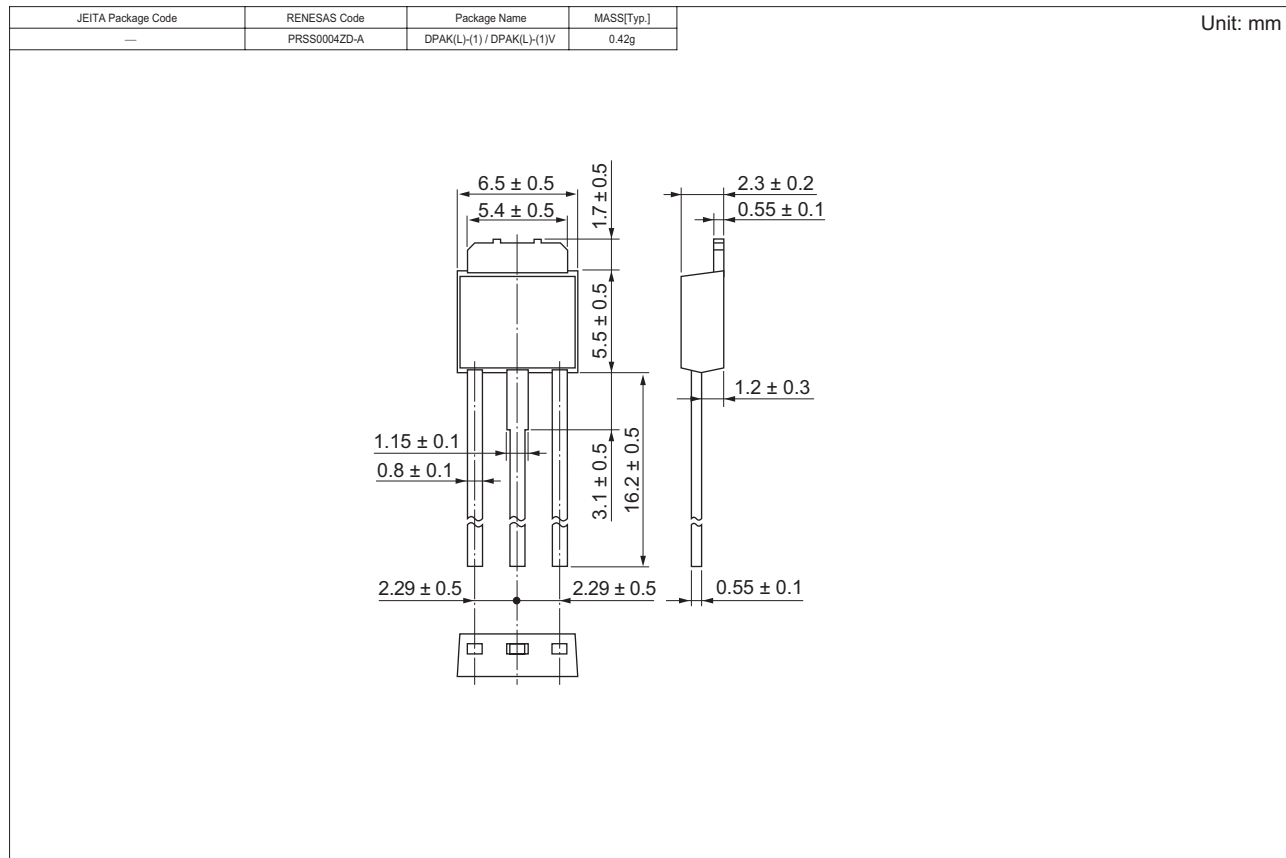


Avalanche Waveform





Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SK2796L-E	3200 pcs	Box (Sack)
2SK2796STL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.